Quad 2-input NAND Schmitt trigger

Rev. 1 — 8 November 2013

**Product data sheet** 

### 1. General description

The 74AHC132-Q100; 74AHCT132-Q100 is a high-speed Si-gate CMOS device and is pin compatible with Low-power Schottky TTL (LSTTL). It is specified in compliance with JEDEC standard No. 7-A.

The 74AHC132-Q100; 74AHCT132-Q100 contains four 2-input NAND gates which accept standard input signals. They can transform slowly changing input signals into sharply defined, jitter free output signals. The gate switches at different points for positive-going and negative-going signals. The difference between the positive voltage  $V_{T+}$  and the negative  $V_{T-}$  is defined as the hysteresis voltage  $V_{H}$ .

This product has been qualified to the Automotive Electronics Council (AEC) standard Q100 (Grade 1) and is suitable for use in automotive applications.

### 2. Features and benefits

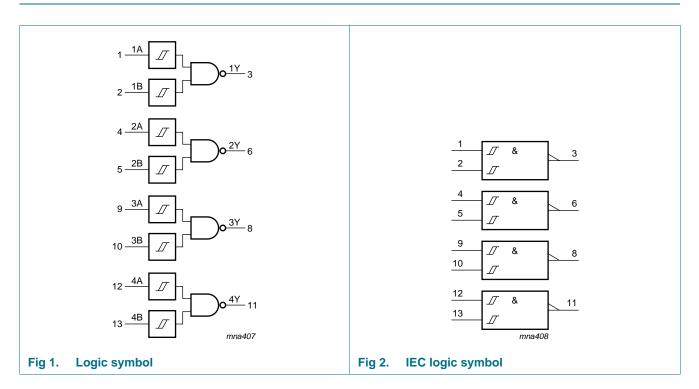
- Automotive product qualification in accordance with AEC-Q100 (Grade 1)
  - Specified from –40 °C to +85 °C and from –40 °C to +125 °C
- Balanced propagation delays
- Inputs accept voltages higher than V<sub>CC</sub>
- Input levels:
  - For 74AHC132-Q100: CMOS level
  - For 74AHCT132-Q100: TTL level
- ESD protection:
  - MIL-STD-883, method 3015 exceeds 2000 V
  - HBM JESD22-A114F exceeds 2000 V
  - MM EIA/JESD22-A115-A exceeds 200 V
- Multiple package options

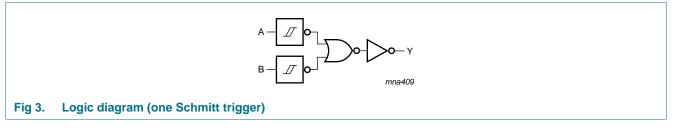


## 3. Ordering information

Table 1. Ordering in	offormation									
Type number	Package									
	Temperature range	Name	Description	Version						
74AHC132D-Q100	–40 °C to +125 °C	SO14	plastic small outline package; 14 leads;	SOT108-1						
74AHCT132D-Q100			body width 3.9 mm							
74AHC132PW-Q100	–40 °C to +125 °C	TSSOP14	plastic thin shrink small outline package; 14 leads;	SOT402-1						
74AHCT132PW-Q100			body width 4.4 mm							
74AHC132BQ-Q100	–40 °C to +125 °C	DHVQFN14	plastic dual in-line compatible thermal enhanced	SOT762-1						
74AHCT132BQ-Q100			very thin quad flat package; no leads; 14 terminals; body $2.5 \times 3 \times 0.85$ mm							

## 4. Functional diagram

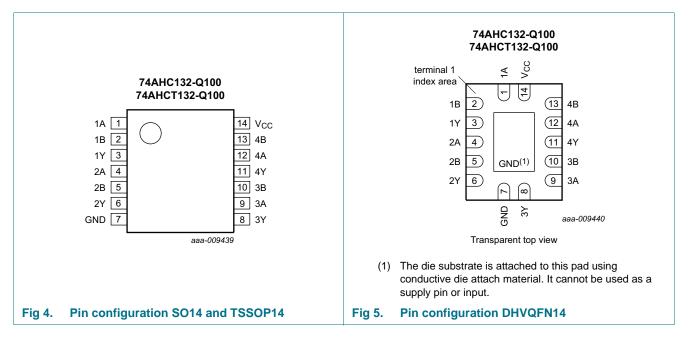




**Quad 2-input NAND Schmitt trigger** 

## 5. Pinning information

### 5.1 Pinning



### 5.2 Pin description

#### Table 2.Pin description

Symbol	Pin	Description
1A, 2A, 3A, 4A	1, 4, 9, 12	data input nA
1B, 2B, 3B, 4B	2, 5, 10, 13	data input nB
1Y, 2Y, 3Y, 4Y	3, 6, 8, 11	data output nY
GND	7	ground (0 V)
V <sub>CC</sub>	14	supply voltage

## 6. Functional description

Table 3.	Function table <sup>[1]</sup>		
Input			Output
nA		nB	nY
L		L	н
L		Н	Н
Н		L	Н
Н		Н	L

[1] H = HIGH voltage level;

L = LOW voltage level.

**Quad 2-input NAND Schmitt trigger** 

## 7. Limiting values

#### Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

				.0	,
Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>CC</sub>	supply voltage		-0.5	+7.0	V
VI	input voltage		-0.5	+7.0	V
I <sub>IK</sub>	input clamping current	V <sub>1</sub> < -0.5 V	<u>[1]</u> –20	-	mA
I <sub>OK</sub>	output clamping current	$V_{\rm O}$ < –0.5 V or $V_{\rm O}$ > $V_{\rm CC}$ + 0.5 V	<u>[1]</u> –20	+20	mA
lo	output current	$V_{O}$ = -0.5 V to (V <sub>CC</sub> + 0.5 V)	-25	+25	mA
I <sub>CC</sub>	supply current		-	+75	mA
I <sub>GND</sub>	ground current		-75	-	mA
T <sub>stg</sub>	storage temperature		-65	+150	°C
P <sub>tot</sub>	total power dissipation	$T_{amb} = -40 \ ^{\circ}C \ to \ +125 \ ^{\circ}C$	[2] _	500	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

For SO14 package: above 70 °C the value of P<sub>tot</sub> derates linearly at 8 mW/K.
 For TSSOP14 package: above 60 °C the value of P<sub>tot</sub> derates linearly at 5.5 mW/K.
 For DHVQFN14 package: above 60 °C the value of P<sub>tot</sub> derates linearly at 4.5 mW/K.

## 8. Recommended operating conditions

#### Table 5.Operating conditions

	1 0					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
74AHC1	32-Q100					
V <sub>CC</sub>	supply voltage		2.0	5.0	5.5	V
VI	input voltage		0	-	5.5	V
Vo	output voltage		0	-	V <sub>CC</sub>	V
T <sub>amb</sub>	ambient temperature		-40	+25	+125	°C
$\Delta t / \Delta V$	input transition rise and fall rate	$V_{CC}$ = 3.0 V to 3.6 V	-	-	100	ns/V
		$V_{CC}$ = 4.5 V to 5.5 V	-	-	20	ns/V
74AHCT	132-Q100					
V <sub>CC</sub>	supply voltage		4.5	5.0	5.5	V
VI	input voltage		0	-	5.5	V
Vo	output voltage		0	-	V <sub>CC</sub>	V
T <sub>amb</sub>	ambient temperature		-40	+25	+125	°C
$\Delta t / \Delta V$	input transition rise and fall rate	$V_{CC}$ = 4.5 V to 5.5 V	-	-	20	ns/V

# 9. Static characteristics

#### Table 6. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		25 °C		–40 °C t	o +85 °C	–40 °C to	o +125 °C	Un
			Min	Тур	Max	Min	Max	Min	Max	
74AHC1	32-Q100								1	
V <sub>OH</sub>	HIGH-level	$V_I = V_{T+} \text{ or } V_{T-}$								
	output voltage	$I_{O}$ = -50 $\mu$ A; $V_{CC}$ = 2.0 V	1.9	2.0	-	1.9	2.2	1.9	-	V
		$I_{O} = -50 \ \mu A; V_{CC} = 3.0 \ V$	2.9	3.0	-	2.9	3.15	2.9	-	V
		$I_{O}$ = -50 $\mu$ A; $V_{CC}$ = 4.5 V	4.4	4.5	-	4.4	3.85	4.4	-	V
		$I_{O}$ = -4.0 mA; $V_{CC}$ = 3.0 V	2.58	-	-	2.48	-	2.40	-	V
		$I_{O}$ = -8.0 mA; $V_{CC}$ = 4.5 V	3.94	-	-	3.80	-	3.70	-	V
V <sub>OL</sub>	LOW-level	$V_I = V_{T+} \text{ or } V_{T-}$								
	output voltage	$I_0 = 50 \ \mu A; \ V_{CC} = 2.0 \ V$	-	0	0.1	-	0.1	-	0.1	V
		$I_0 = 50 \ \mu A; \ V_{CC} = 3.0 \ V$	-	0	0.1	-	0.1	-	0.1	V
		$I_0 = 50 \ \mu A; \ V_{CC} = 4.5 \ V$	-	0	0.1	-	0.1	-	0.1	V
		$I_0 = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.36	-	0.44	-	0.55	V
		$I_0 = 8.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	-	-	0.36	-	0.44	-	0.55	V
I	input leakage current	$V_1 = 5.5 V \text{ or GND};$ $V_{CC} = 0 V \text{ to } 5.5 V$	-	-	0.1	-	1.0	-	2.0	μA
I <sub>CC</sub>	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 5.5$ V	-	-	2.0	-	20	-	40	μΑ
Cı	input capacitance	$V_I = V_{CC}$ or GND	-	3	10	-	10	-	10	рF
Co	output capacitance		-	4	-	-	-	-	-	рF
74AHCT	132-Q100									
V <sub>он</sub>	HIGH-level	$V_{I} = V_{T+} \text{ or } V_{T-}; V_{CC} = 4.5 \text{ V}$								
	output voltage	I <sub>O</sub> = -50 μA	4.4	4.5	-	4.4	-	4.4	-	V
		I <sub>O</sub> = -8.0 mA	3.94	-	-	3.80	-	3.70	-	V
V <sub>OL</sub>	LOW-level	$V_{I} = V_{T+} \text{ or } V_{T-}; V_{CC} = 4.5 \text{ V}$								
	output voltage	I <sub>O</sub> = 50 μA	-	0	0.1	-	0.1	-	0.1	V
		I <sub>O</sub> = 8.0 mA	-	-	0.36	-	0.44	-	0.55	V
I	input leakage current	$V_1 = 5.5 V \text{ or GND};$ $V_{CC} = 0 V \text{ to } 5.5 V$	-	-	0.1	-	1.0	-	2.0	μΑ
I <sub>CC</sub>	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 5.5$ V	-	-	2.0	-	20	-	40	μA
∆I <sub>CC</sub>	additional supply current	per input pin; $V_I = V_{CC} - 2.1 \text{ V}$ ; other pins at $V_{CC}$ or GND; $I_O = 0 \text{ A}$ ; $V_{CC} = 4.5 \text{ V}$ to 5.5 V	-	-	1.35	-	1.5	-	1.5	m
CI	input capacitance	$V_{I} = V_{CC} \text{ or } GND$	-	3	10	-	10	-	10	рF
Co	output capacitance		-	4	-	-	-	-	-	pF

## **10.** Dynamic characteristics

#### Table 7. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit, see <u>Figure 7</u>.

Symbol	Parameter	Conditions		25 °C		<b>−40</b> °C t	to +85 °C	-40 °C te	o +125 °C	Unit
				Typ <mark>[1]</mark>	Max	Min	Max	Min	Max	
74AHC1	32-Q100	1								
t <sub>pd</sub>	propagation	nA, nB to nY; see Figure 6	2]							
	delay	$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$								
		C <sub>L</sub> = 15 pF	-	4.4	11.9	1.0	14.0	1.0	15.0	ns
		C <sub>L</sub> = 50 pF	-	6.2	15.4	1.0	17.5	1.0	19.5	ns
		$V_{CC}$ = 4.5 V to 5.5 V								
		C <sub>L</sub> = 15 pF	-	3.3	7.7	1.0	9.0	1.0	10.0	ns
		C <sub>L</sub> = 50 pF	-	4.7	9.7	1.0	11.0	1.0	12.5	ns
C <sub>PD</sub>	power dissipation capacitance	$f_i = 1 \text{ MHz}; V_1 = \text{GND to } V_{\text{CC}}$	3] -	11	-	-	-	-	-	pF
74AHCT	132-Q100									
t <sub>pd</sub>	propagation	nA, nB to nY; see Figure 6	2]							
	delay	$V_{CC}$ = 4.5 V to 5.5 V								
		C <sub>L</sub> = 15 pF	-	3.5	7.0	1.0	8.0	1.0	9.0	ns
		C <sub>L</sub> = 50 pF	-	5.0	8.0	1.0	9.0	1.0	10.0	ns
C <sub>PD</sub>	power dissipation capacitance	$f_i = 1 \text{ MHz}; V_1 = \text{GND to } V_{\text{CC}}$	<u>3]</u>	14	-	-	-	-	-	pF

[1] Typical values are measured at nominal supply voltage (V<sub>CC</sub> = 3.3 V and V<sub>CC</sub> = 5.0 V).

[2]  $t_{pd}$  is the same as  $t_{PLH}$  and  $t_{PHL}$ .

[3]  $C_{PD}$  is used to determine the dynamic power dissipation (P<sub>D</sub> in  $\mu$ W).

 $P_{D} = C_{PD} \times V_{CC}^{2} \times f_{i} \times N + \Sigma (C_{L} \times V_{CC}^{2} \times f_{o}) \text{ where:}$ 

 $f_i = input frequency in MHz;$ 

f<sub>o</sub> = output frequency in MHz;

 $C_L$  = output load capacitance in pF;

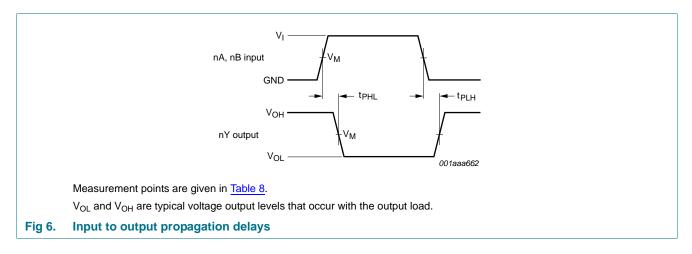
 $V_{CC}$  = supply voltage in V;

N = number of inputs switching;

 $\Sigma(C_L \times V_{CC}^2 \times f_0)$  = sum of the outputs.

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## 11. Waveforms



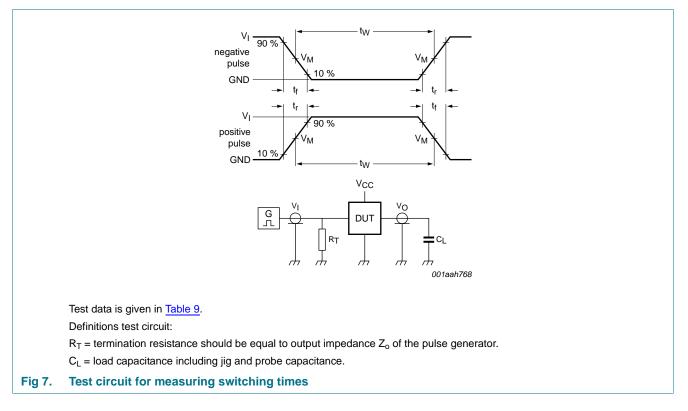
#### Table 8.Measurement points

Туре	Input	Output
	V <sub>M</sub>	V <sub>M</sub>
74AHC132-Q100	$0.5  imes V_{CC}$	$0.5 \times V_{CC}$
74AHCT132-Q100	1.5 V	$0.5 \times V_{CC}$

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#### Table 9. Test data

Туре	Input L		Load	Test
	VI	t <sub>r</sub> , t <sub>f</sub>	CL	
74AHC132-Q100	V <sub>CC</sub>	$\leq$ 3.0 ns	50 pF, 15 pF	t <sub>PLH</sub> , t <sub>PHL</sub>
74AHCT132-Q100	3.0 V	$\leq$ 3.0 ns	50 pF, 15 pF	t <sub>PLH</sub> , t <sub>PHL</sub>

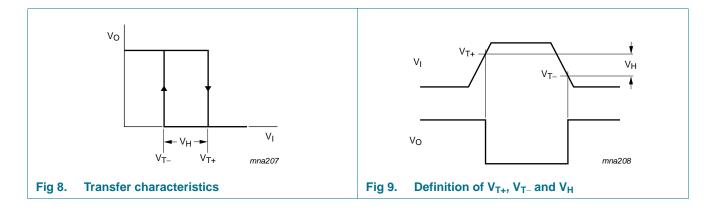
## **12. Transfer characteristics**

#### Table 10. Transfer characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		25 °C		<b>−40</b> °C t	o +85 °C	–40 °C to	o +125 °C	Unit
			Min	Тур	Max	Min	Max	Min	Max	
74AHC1	32-Q100	· ·								
V <sub>T+</sub>	positive-going threshold	$V_{CC} = 3.0 V$	-	-	2.2	-	2.2	-	2.2	V
	voltage	$V_{CC} = 4.5 V$	-	-	3.15	-	3.15	-	3.15	V
		$V_{CC} = 5.5 V$	-	-	3.85	-	3.85	-	3.85	V
$V_{T-}$	negative-going threshold	$V_{CC} = 3.0 V$	0.9	-	-	0.9	-	0.9	-	V
	voltage	$V_{CC} = 4.5 V$	1.35	-	-	1.35	-	1.35	-	V
		$V_{CC} = 5.5 V$	1.65	-	-	1.65	-	1.65	-	V
V <sub>H</sub>	hysteresis voltage	$V_{CC} = 3.0 V$	0.3	-	1.2	0.3	1.2	0.25	1.2	V
		$V_{CC} = 4.5 V$	0.4	-	1.4	0.4	1.4	0.35	1.4	V
		$V_{CC} = 5.5 V$	0.5	-	1.6	0.5	1.6	0.45	1.6	V
74AHCT	132-Q100									
V <sub>T+</sub>	positive-going threshold	$V_{CC} = 4.5 V$	-	-	1.9	-	1.9	-	1.9	V
	voltage	$V_{CC} = 5.5 V$	-	-	2.1	-	2.1	-	2.1	V
V <sub>T-</sub>	negative-going threshold	$V_{CC} = 4.5 V$	0.5	-	-	0.5	-	0.5	-	V
	voltage	$V_{CC} = 5.5 V$	0.6	-	-	0.6	-	0.6	-	V
V <sub>H</sub>	hysteresis voltage	$V_{CC}$ = 4.5 V	0.3	-	1.4	0.3	1.4	0.3	1.4	V
		$V_{CC} = 5.5 V$	0.3	-	1.5	0.3	1.5	0.3	1.5	V

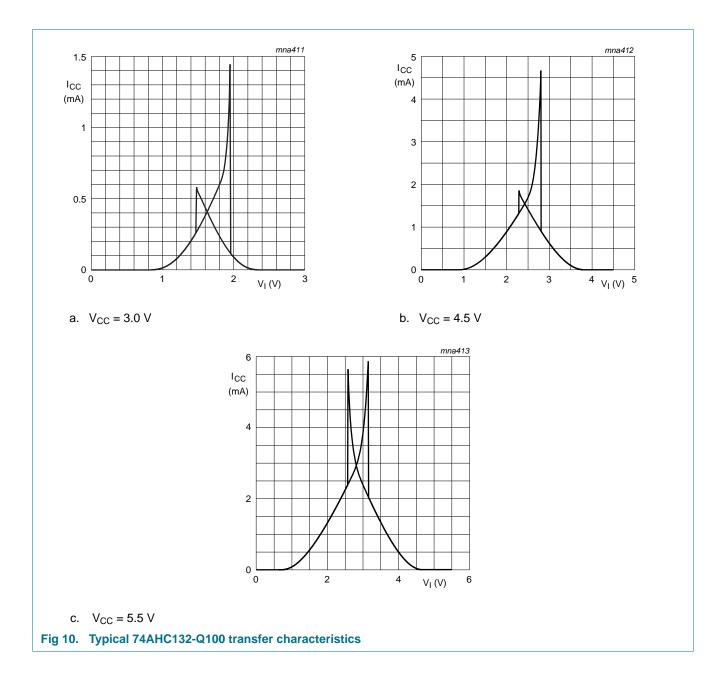
### **13. Transfer characteristics waveforms**



### **NXP Semiconductors**

# 74AHC132-Q100; 74AHCT132-Q100

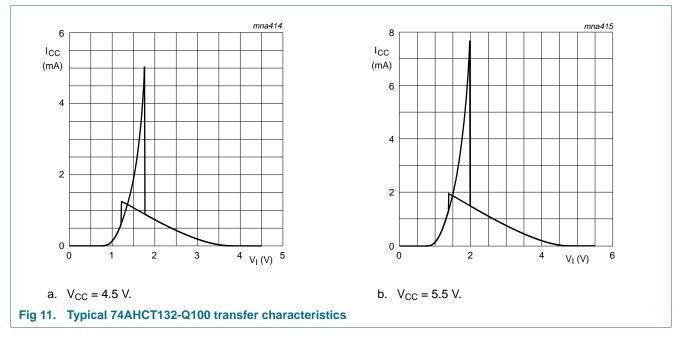
Quad 2-input NAND Schmitt trigger



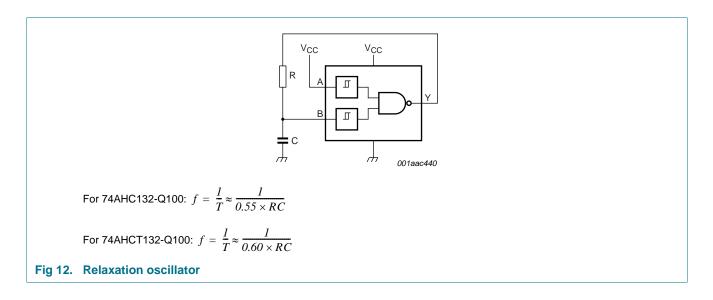
### **NXP Semiconductors**

# 74AHC132-Q100; 74AHCT132-Q100

**Quad 2-input NAND Schmitt trigger** 

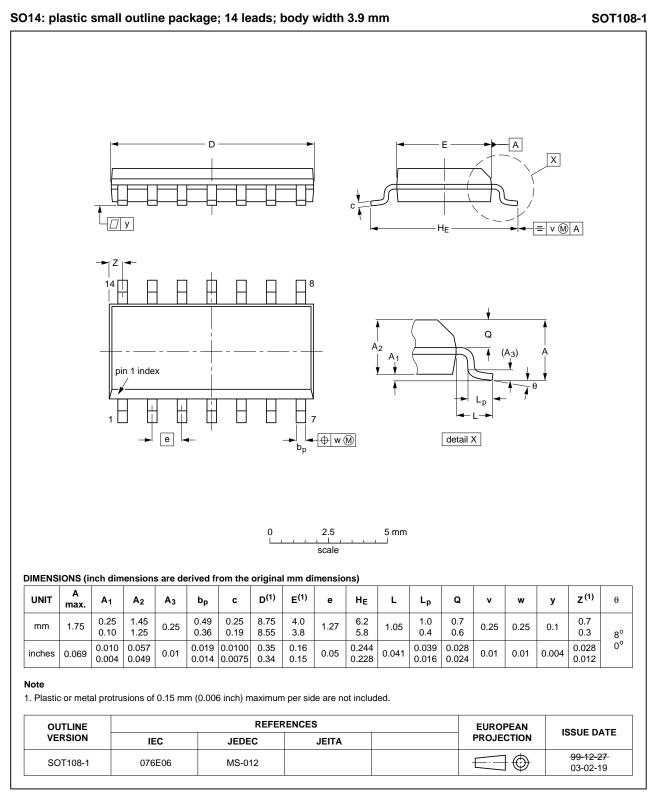


# 14. Application information



**Quad 2-input NAND Schmitt trigger** 

## 15. Package outline



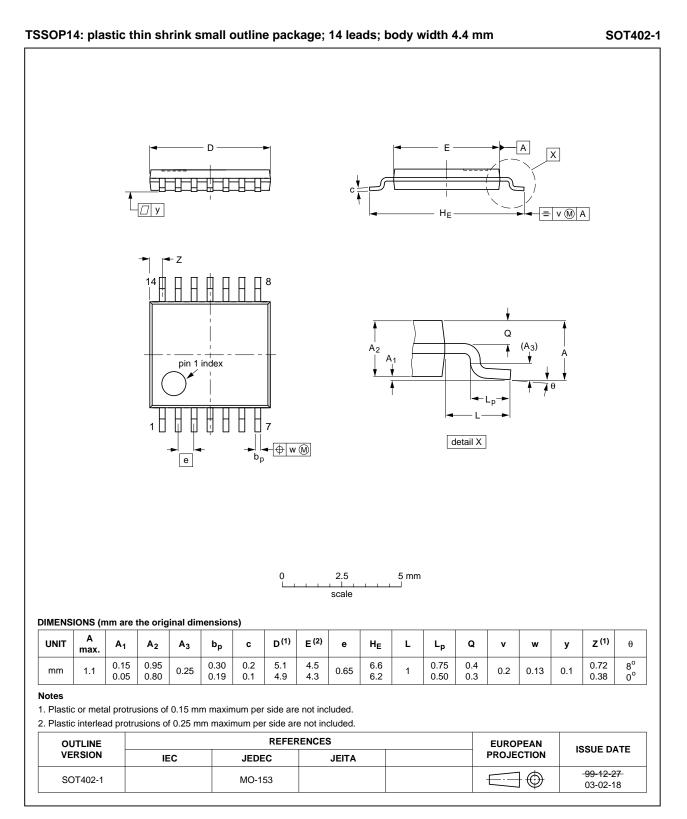
#### Fig 13. Package outline SOT108-1 (SO14)

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74AHC\_AHCT132\_Q100

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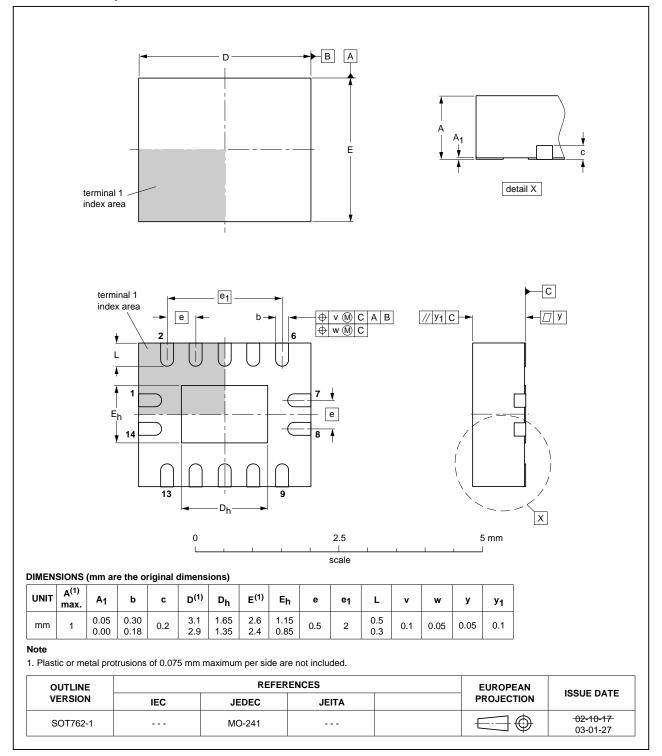
**Quad 2-input NAND Schmitt trigger** 



#### Fig 14. Package outline SOT402-1 (TSSOP14)

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Quad 2-input NAND Schmitt trigger



#### DHVQFN14: plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 14 terminals; body 2.5 x 3 x 0.85 mm SOT762-1

Fig 15. Package outline SOT762-1 (DHVQFN14)

Quad 2-input NAND Schmitt trigger

# **16. Abbreviations**

AcronymDescriptionCDMCharged Device ModelCMOSComplementary Metal-Oxide SemiconductorDUTDevice Under TestESDElectroStatic DischargeHBMHuman Body ModelLSTTLLow-power Schottky Transistor-Transistor LogicMILMilitaryMMMachine Model	Table 11.	Abbreviations
CMOSComplementary Metal-Oxide SemiconductorDUTDevice Under TestESDElectroStatic DischargeHBMHuman Body ModelLSTTLLow-power Schottky Transistor-Transistor LogicMILMilitary	Acronym	Description
DUTDevice Under TestESDElectroStatic DischargeHBMHuman Body ModelLSTTLLow-power Schottky Transistor-Transistor LogicMILMilitary	CDM	Charged Device Model
ESDElectroStatic DischargeHBMHuman Body ModelLSTTLLow-power Schottky Transistor-Transistor LogicMILMilitary	CMOS	Complementary Metal-Oxide Semiconductor
HBM     Human Body Model       LSTTL     Low-power Schottky Transistor-Transistor Logic       MIL     Military	DUT	Device Under Test
LSTTL     Low-power Schottky Transistor-Transistor Logic       MIL     Military	ESD	ElectroStatic Discharge
MIL Military	HBM	Human Body Model
····· ································	LSTTL	Low-power Schottky Transistor-Transistor Logic
MM Machine Model	MIL	Military
	MM	Machine Model

# 17. Revision history

Table 12.    Revision history				
Document ID	Release date	Data sheet status	Change notice	Supersedes
74AHC_AHCT132_Q100 v.1	20131108	Product data sheet	-	-

## **18. Legal information**

### 18.1 Data sheet status

Document status[1][2]	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <a href="http://www.nxp.com">http://www.nxp.com</a>.

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